

General purpose (dual digital transistors)

UMB2N / IMB2A

●Features

- 1) Two DTA144E chips in a UMT or SMT package.
- 2) Same size as UMT3 or SMT3 package, so same mounting machine can be used for both.
- 3) Transistor elements are independent, eliminating interference.

●Structure

Epitaxial planar type
PNP silicon transistor
(Built-in resistor type)

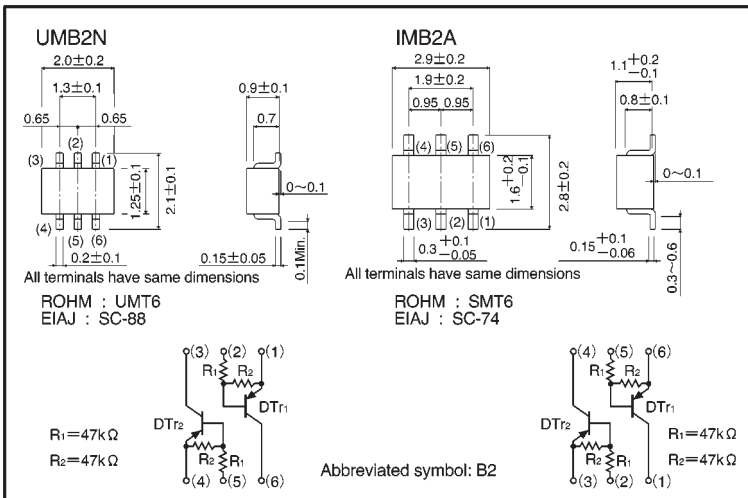
The following characteristics apply to both DT_{r1} and DT_{r2}.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _i	-40	V
		10	
Output current	I _o	-30	mA
	I _{C(Max.)}	-100	
Power dissipation	UMB2N	150 (TOTAL)	*1
	IMB2A	300 (TOTAL)	*2
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.
*2 200mW per element must not be exceeded.

●External dimensions (Units: mm)



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	—	—	-0.5	V	$V_{CC} = -5V, I_o = -100 \mu A$
	$V_{I(on)}$	-3	—	—		$V_o = -0.3V, I_o = -2mA$
Output voltage	$V_{O(on)}$	—	-0.1	-0.3	V	$I_o/I_i = -10mA/-0.5mA$
Input current	I_i	—	—	-0.18	mA	$V_i = -5V$
Output current	$I_{O(off)}$	—	—	-0.5	μA	$V_{CC} = -50V, V_i = 0V$
DC current gain	G_i	68	—	—	—	$V_o = -5V, I_o = -5mA$
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = -10mA, I_E = 5mA, f = 100MHz$ *
Input resistance	R_i	32.9	47	61.1	k Ω	—
Resistance ratio	R_2/R_1	0.8	1	1.2	—	—

* Transition frequency of the device

● Packaging specifications

Part No.	Packaging type	Taping	
	Code	TN	T110
	Basic ordering unit (pieces)	3000	3000
UMB2N		○	—
IMB2A		—	○

● Electrical characteristic curves

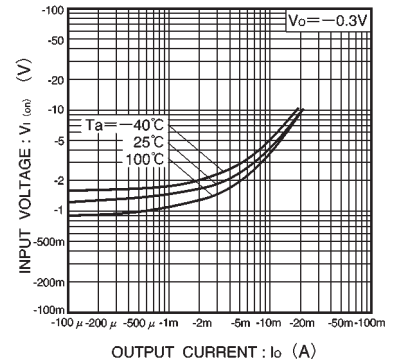


Fig.1 Input voltage vs. output current (ON characteristics)

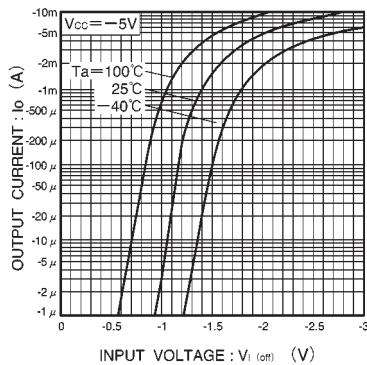


Fig.2 Output current vs. input voltage (OFF characteristics)

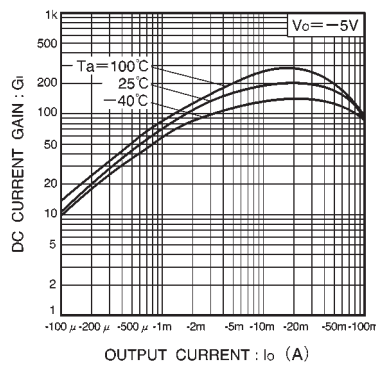


Fig.3 DC current gain vs. output current

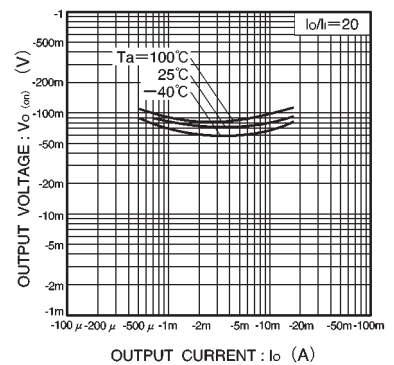


Fig.4 Output voltage vs. output current